

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10	(US-20060163605-\$).did. or (US-6001748-\$ or US-5668524-\$ or US-5766783-\$).did. or (WO-2005003414-\$ or WO-2004005216-\$).did. or (JP-04092866-\$ or JP-04092865-\$). did. or (WO-2004005216-\$ or WO-2005003414-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 06:34
L2	1	(rough roughness) and L1	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 06:34
L3	71	((sintered with compact) same (rough roughness)) and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 08:10
L4	5	((sintered with compact) same (rough roughness)) and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) and (specific adj resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 08:10
L5	1250	(conduction adj via)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 08:27
L6	36	(conduction adj via) and semiconductor and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 08:30

EAST Search History

L7	23	(conduction adj via) and semiconductor and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) and (thin near3 film)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 08:42
L8	50	(substrate same (conduction with channel)) and semiconductor and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride)) and (thin near3 film)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 08:42
S1	78	kenichiro.inv. and miyahara.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/02 13:00
S2	2	((("6001748") or ("5668524"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/08/02 12:40
S3	1	((thin adj film) with (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))) and ((sinter\$ adj compact) with (AlN (aluminum adj nitride))) and (hexagonal trogonal) and (optical with permeab\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/03 08:37
S4	3	(trigonal hexagonal) and (S1 S2 S3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/02 15:17

EAST Search History

S5	32	((thin adj film) with (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))) and (sinter\$ with (AlN (aluminum adj nitride))) and (hexagonal trogonal wurtzite)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/08/03 09:25
S6	7	(sintered with compact with ((optical visible light) near3 (permeab\$ transpar\$))) and (GALLIUMNITRID GALLIUMNITRIDE GALLIUMNITRIDE-BASED INDIUMNITRIDE ALUMINUMNITRIDE ALUMINUMNITRIDE-BASED GaN (gallium adj nitride) InN (indium adj nitride) AlN (aluminum adj nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2007/02/20 06:38